

MOSFET - Power, Single N-Channel, TOLL 80 V, 1.05 mΩ, 351 A

NVBLS1D1N08H

Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- AEC-Q101 Qualified and PPAP Capable
- Lowers Switching Noise/EMI
- These Devices are Pb-Free and are RoHS Compliant

Typical Applications

- Power Tools, Battery Operated Vacuums
- UAV/Drones, Material Handling
- BMS/Storage, Home Automation

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V_{DSS}	80	V
Gate-to-Source Voltage			V_{GS}	± 20	V
Continuous Drain Current $R_{\theta JC}$ (Notes 1, 3)	Steady State	$T_C = 25^\circ\text{C}$	I_D	351	A
		$T_C = 100^\circ\text{C}$		248	
Power Dissipation $R_{\theta JC}$ (Note 1)	Steady State	$T_C = 25^\circ\text{C}$	P_D	311	W
		$T_C = 100^\circ\text{C}$		156	
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2, 3)	Steady State	$T_A = 25^\circ\text{C}$	I_D	41	A
		$T_A = 100^\circ\text{C}$		29	
Power Dissipation $R_{\theta JA}$ (Notes 1, 2)	Steady State	$T_A = 25^\circ\text{C}$	P_D	4.2	W
		$T_A = 100^\circ\text{C}$		2.1	
Pulsed Drain Current	$T_A = 25^\circ\text{C}$, $t_p = 10 \mu\text{s}$		I_{DM}	900	A
Operating Junction and Storage Temperature Range			T_J , T_{stg}	-55 to +175	$^\circ\text{C}$
Source Current (Body Diode)			I_S	259	A
Single Pulse Drain-to-Source Avalanche Energy ($I_{L(pk)} = 31.9 \text{ A}$)			E_{AS}	1580	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case - Steady State	$R_{\theta JC}$	0.48	$^\circ\text{C/W}$
Junction-to-Ambient - Steady State (Note 2)	$R_{\theta JA}$	35.8	

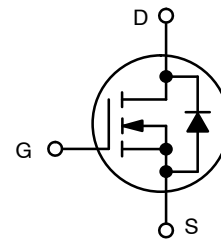
1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.



ON Semiconductor®

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$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
80 V	1.05 mΩ @ 10 V	351 A

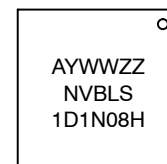


N-CHANNEL MOSFET



TOLL
CASE 100CU

MARKING DIAGRAM



NVBLS1D1N08H = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

NVBLS1D1N08H

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	80			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			57		mV/ $^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 80\text{ V}$	$T_J = 25\text{ }^\circ\text{C}$		10	μA
			$T_J = 125^\circ\text{C}$		250	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = 20\text{ V}$			100	nA

ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 650\text{ }\mu\text{A}$	2.0	2.9	4.0	V
Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			-7.7		mV/ $^\circ\text{C}$
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 50\text{ A}$		0.92	1.05	m Ω
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{ V}, I_D = 50\text{ A}$		213		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 40\text{ V}$		11200		pF
Output Capacitance	C_{OSS}			1600		
Reverse Transfer Capacitance	C_{RSS}			49		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 64\text{ V}, I_D = 50\text{ A}$		166		nC
Threshold Gate Charge	$Q_{G(TH)}$			29		
Gate-to-Source Charge	Q_{GS}			44		
Gate-to-Drain Charge	Q_{GD}			35		
Plateau Voltage	V_{GP}			4		V

SWITCHING CHARACTERISTICS (Note 5)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 10\text{ V}, V_{DS} = 64\text{ V}, I_D = 50\text{ A}, R_G = 6\text{ }\Omega$		45		ns
Rise Time	t_r			43		
Turn-Off Delay Time	$t_{d(OFF)}$			141		
Fall Time	t_f			43		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 50\text{ A}$	$T_J = 25^\circ\text{C}$		0.76	1.2	V
			$T_J = 125^\circ\text{C}$		0.6		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s}, I_S = 50\text{ A}$			92		ns
Reverse Recovery Charge	Q_{RR}				234		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

5. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

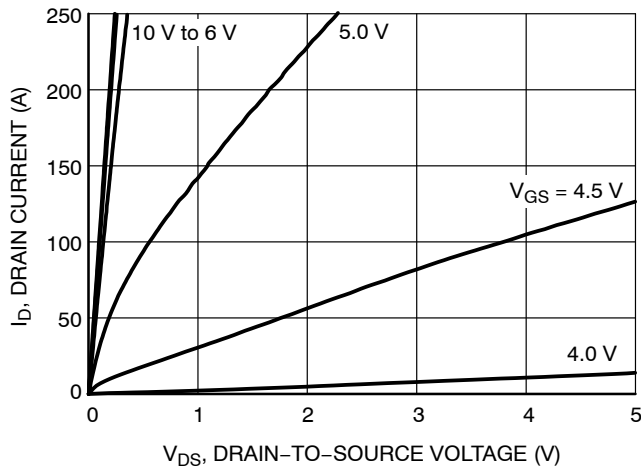


Figure 1. On-Region Characteristics

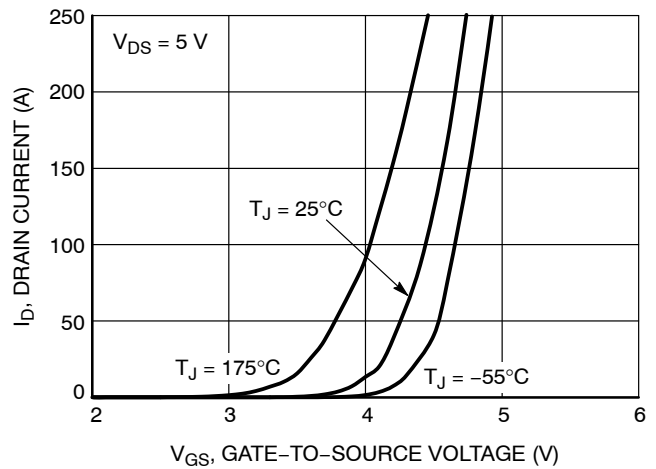


Figure 2. Transfer Characteristics

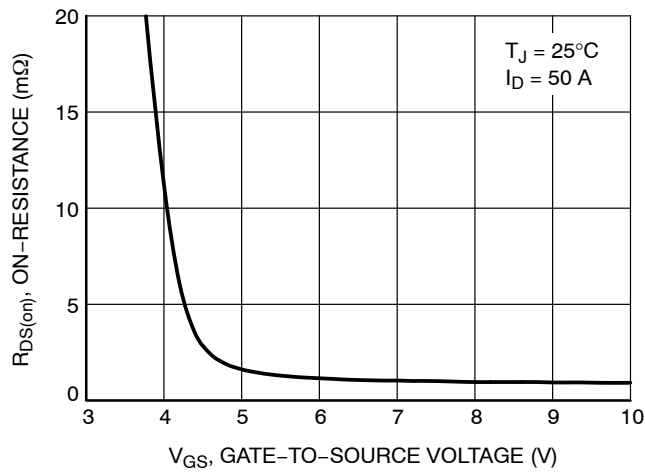


Figure 3. On-Resistance vs. Gate-to-Source Voltage

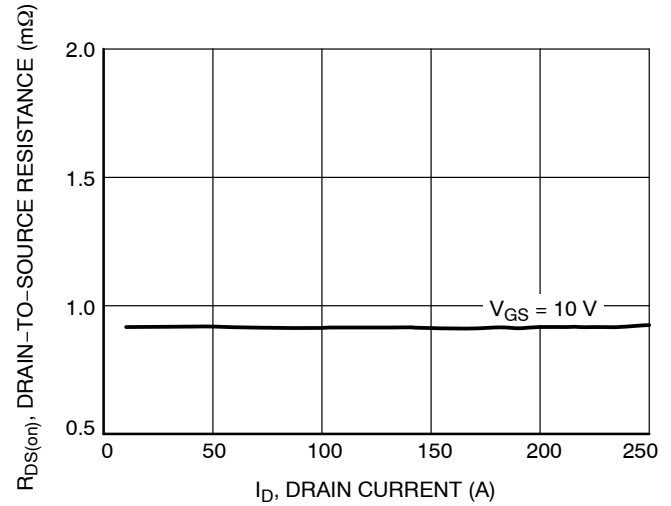


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

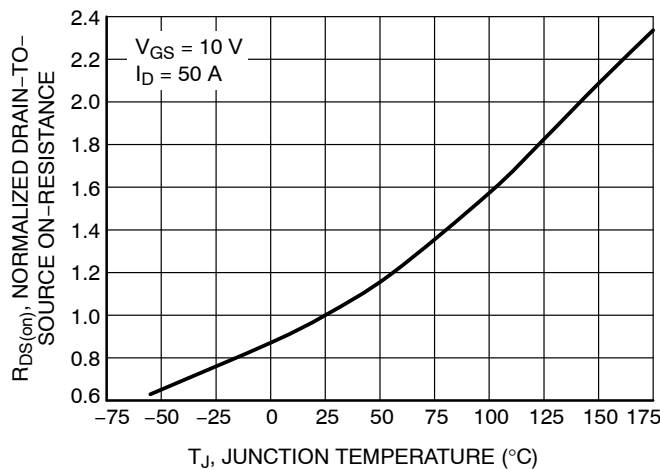


Figure 5. On-Resistance Variation with Temperature

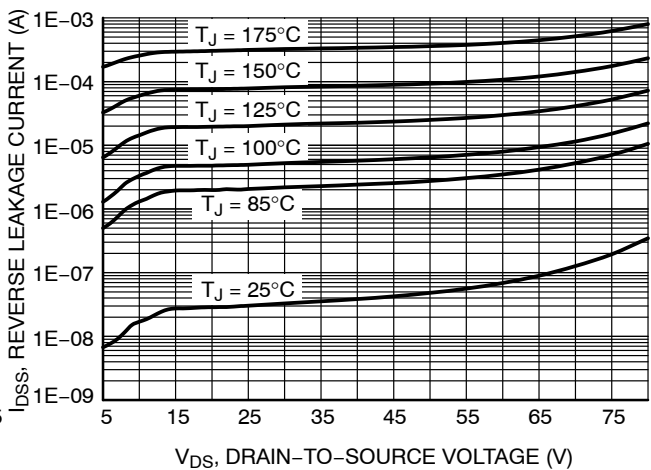


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL CHARACTERISTICS

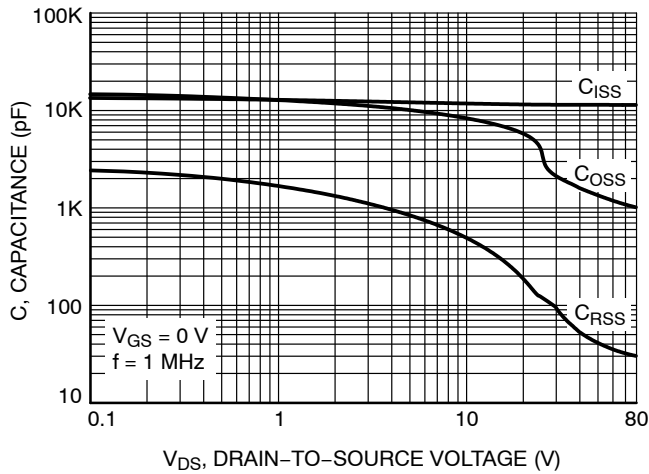


Figure 7. Capacitance Variation

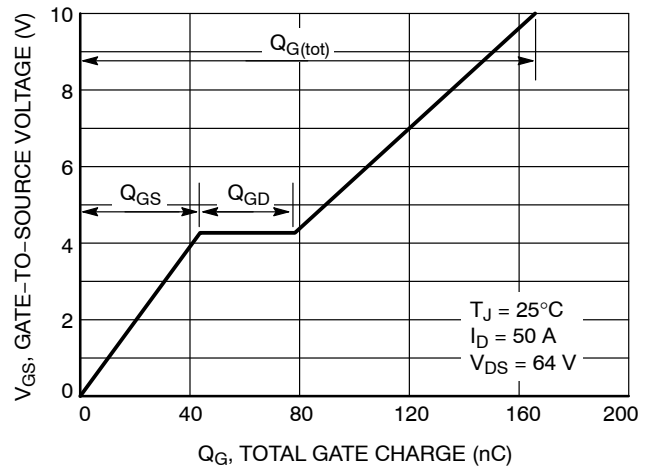


Figure 8. Gate-to-Source Voltage vs. Total Charge

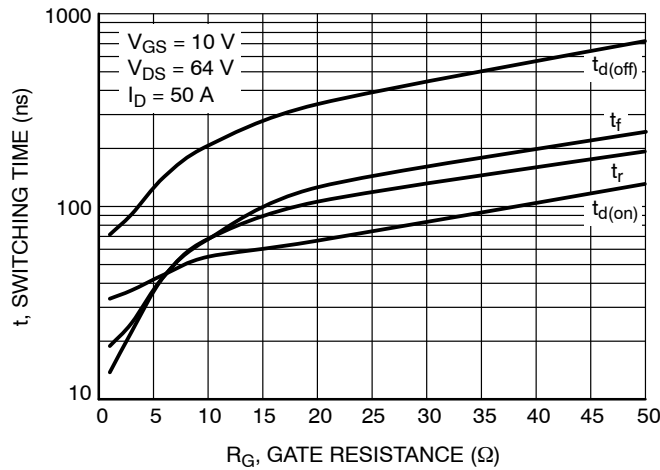


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

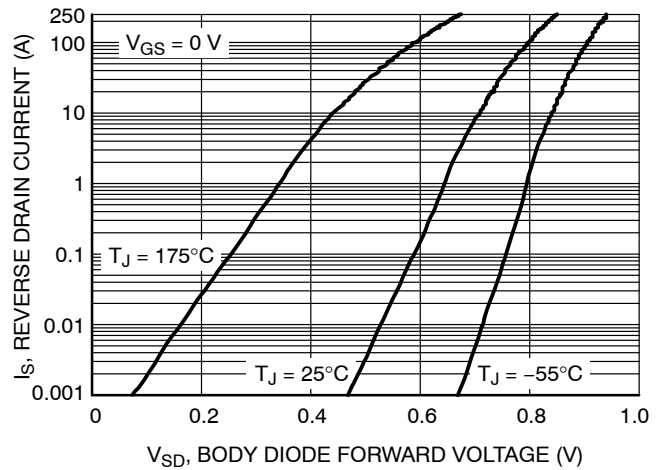


Figure 10. Diode Forward Voltage vs. Current

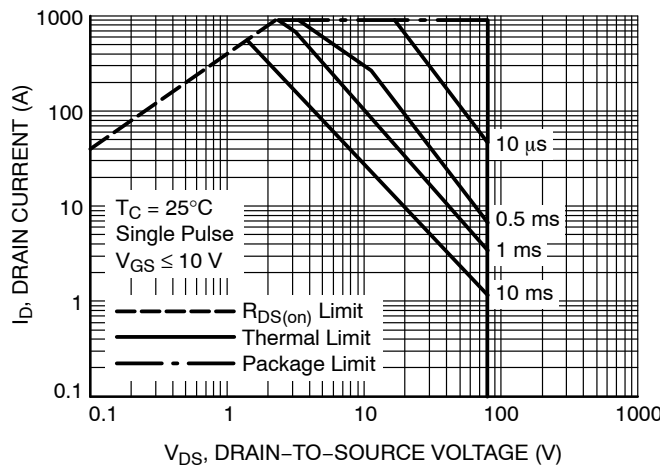


Figure 11. Maximum Rated Forward Biased Safe Operating Area

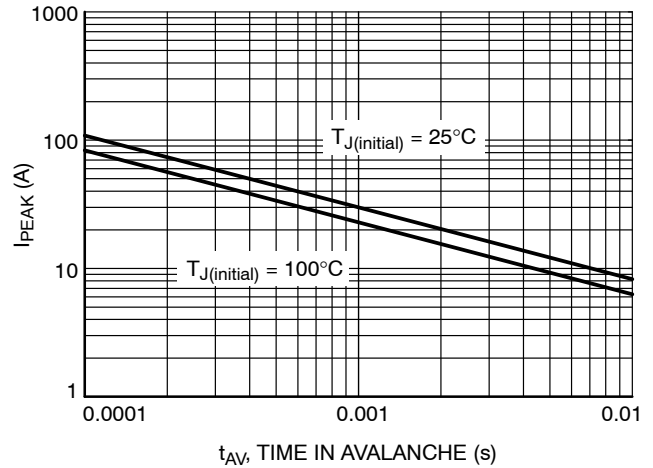


Figure 12. Maximum Drain Current vs. Time in Avalanche

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TYPICAL CHARACTERISTICS

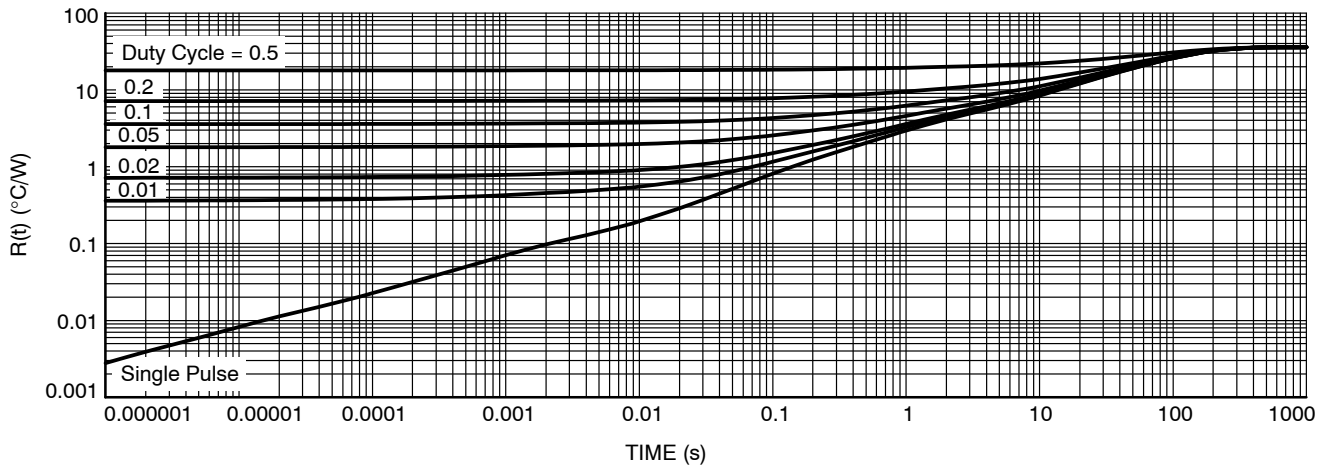


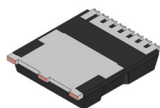
Figure 13. Transient Thermal Impedance

DEVICE ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
NVBLS1D1N08H	NVBLS 1D1N08H	M0-299A (Pb-Free)	2000 / Tape & Reel

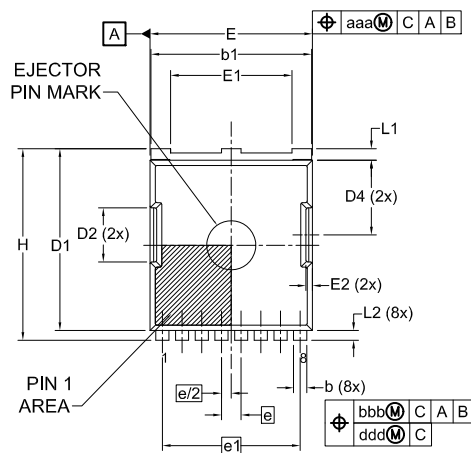
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

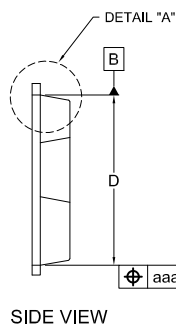


H-PSOF8L 11.68x9.80 CASE 100CU ISSUE C

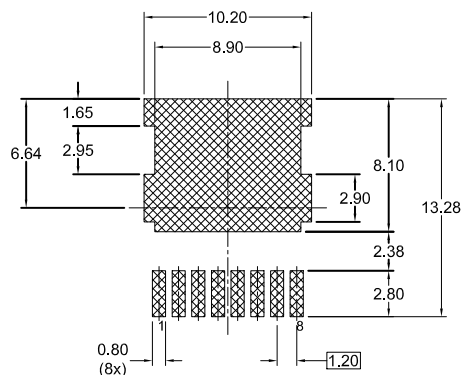
DATE 22 MAY 2023



TOP VIEW

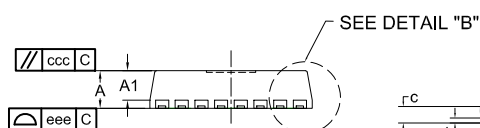


SIDE VIEW



LAND PATTERN RECOMMENDATION

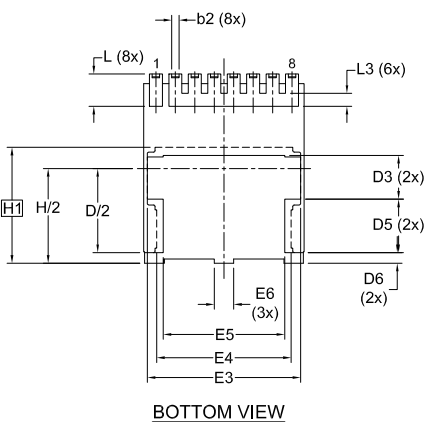
*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.



FRONT VIEW

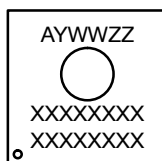
DETAIL "A"
SCALE: 2X

DETAIL "B"
SCALE: 2X



BOTTOM VIEW

GENERIC MARKING DIAGRAM*



A = Assembly Location
Y = Year
WW = Work Week
ZZ = Assembly Lot Code
XXXX = Specific Device Code

- NOTES:
1. PACKAGE STANDARD REFERENCE: JEDEC MO-299, ISSUE A.
 2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
 3. CONTROLLING DIMENSION: MILLIMETERS.
 4. COPLANARITY APPLIES TO THE EXPOSED WELL AS THE TERMINALS.
 5. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
 6. SEATING PLANE IS DEFINED BY THE TERMINALS. "A1" IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	2.20	2.30	2.40
A1	1.70	1.80	1.90
b	0.70	0.80	0.90
b1	9.70	9.80	9.90
b2	0.35	0.45	0.55
c	0.40	0.50	0.60
c1	0.10	—	—
D	10.28	10.38	10.48
D/2	5.09	5.19	5.29
D1	10.98	11.08	11.18
D2	3.20	3.30	3.40
D3	2.60	2.70	2.80
D4	4.45	4.55	4.65
D5	3.20	3.30	3.40
D6	0.55	0.65	0.75
E	9.80	9.90	10.00
E1	7.30	7.40	7.50
E2	0.30	0.40	0.50
E3	9.36	9.46	9.56

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
E4	8.20	8.30	8.40
E5	7.40	7.50	7.60
E6	1.10	1.20	1.30
e	1.20 BSC		
e/2	0.60 BSC		
e1	8.40 BSC		
H	11.58	11.68	11.78
H/2	5.74	5.84	5.94
H1	7.15 BSC		
L	1.90	2.00	2.10
L1	0.60	0.70	0.80
L2	0.50	0.60	0.70
L3	0.70	0.80	0.90
θ	0°	—	12°
aaa	0.20		
bbb	0.25		
ccc	0.20		
ddd	0.20		
eee	0.10		

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "μ", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	H-PSOF8L 11.68x9.80	PAGE 1 OF 1

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